/ Descriptions

DFN1006-2L ṂṂ Ŀ ESD ʒ ï͡ ǁ ˥

DFN1006-2L Plastic Package ESD Protection Diode.

/ Features

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Ultra small package, Response Time is Typically < 1 ns, ESD Rating of Class 3 (> 16 kV) per Human Body Model,IEC61000ɢ4ɢ2 Level 4 ESD Protection, Qualified to AEC-Q101 Standards for High Reliability, HF Product.

/ Applications

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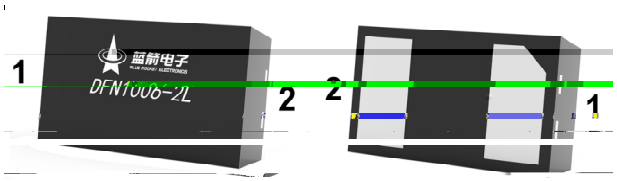
Suitable for cellular phones audio,MP3 players, Digital cameras, Portable devices, mobile telephone and other users, Meet the stringent requirements of automotive applications.





/ Marking

ɔ ʍ ˧ ب ˝ See Marking Instructions.

/ Absolute Maximum Ratings(Ta=25)

v ̈Ω̣ Parameter	ɬ N Symbol	̈Ω̣Ö Rating	D Ɉ Unit
Peak pulse power (t_p = 8/20 s)	P_K	69	W
Peak pulse current (t_p = 8/20 s)	I_{PP}	5.5	A
ESD according to IEC61000-4-2 air discharge	V_{ESD}	±15	KV
ESD according to IEC61000-4-2 contact discharge		±8	
Junction temperature	T_J	150	
Storage temperature	T_{STG}	-55~+150	

/ Electrical Characteristics(Ta=25)

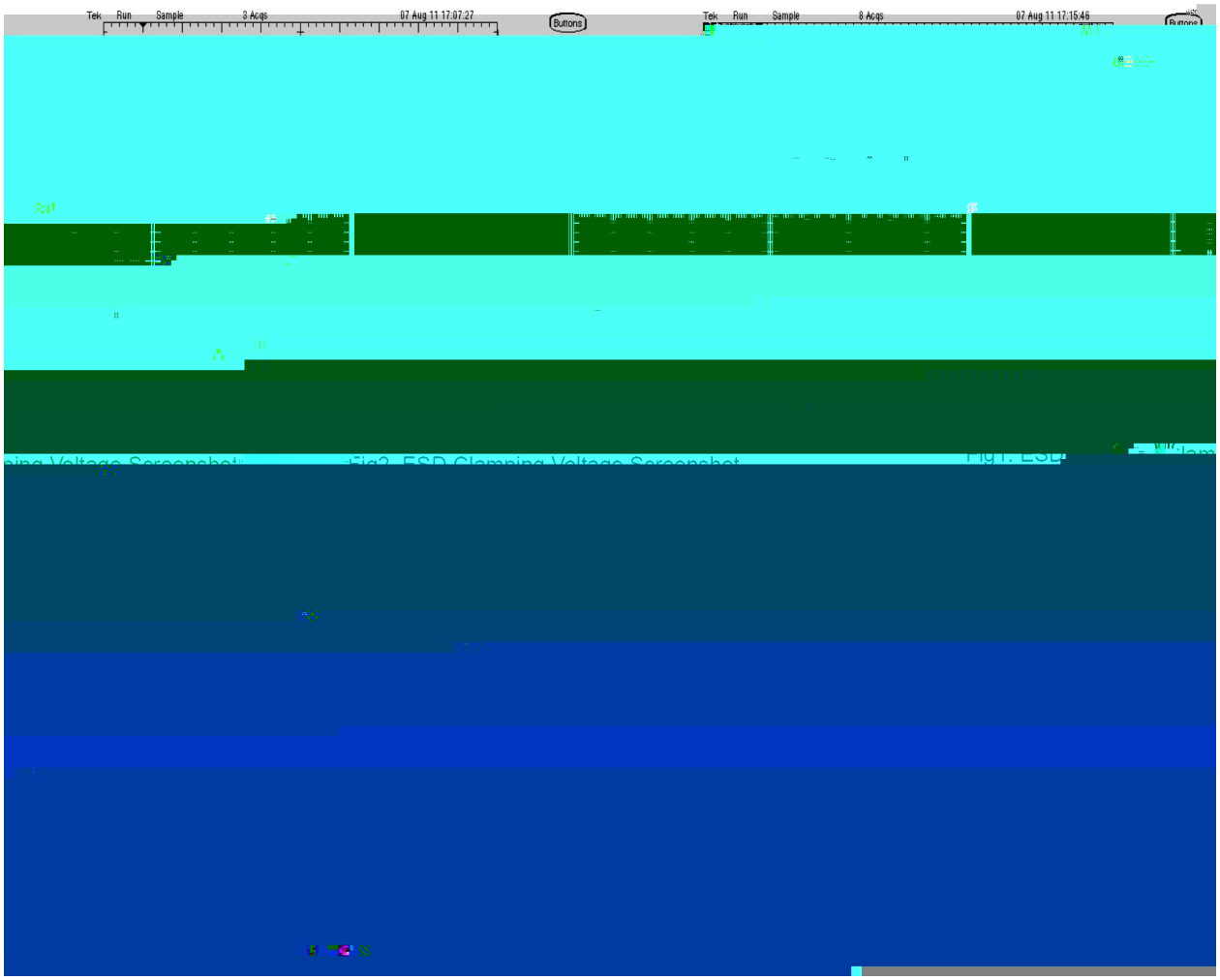
v ̈Ω̣ Parameter	ɬ N Symbol	⊥⊥ ;ɬ Ţ Test Conditions	ω̣ ṇ Ö Min	Ɛ ʒ Ö Typ	ω̣ ʑ Ö Max	D Ɉ Unit
Reverse maximum working voltage	V_{RWM}				5.0	V
Reverse leakage current	I_R	V_{RWM} = 5V			0.5	uA
		V_{RWM} = 3.5V			0.3	uA
Reverse breakdown voltage[1)]	V_{BR}	I_T = 1mA	5.6			V
Clamping voltage [2)]	V_C	I_{PP} = 1A t_p = 8/20 s			9.8	V
		I_{PP} = 5.5A t_p = 8/20 s			12.5	V
Junction capacitance	C_J	V_R = 0V f = 1MHz			15	pF

Notes:

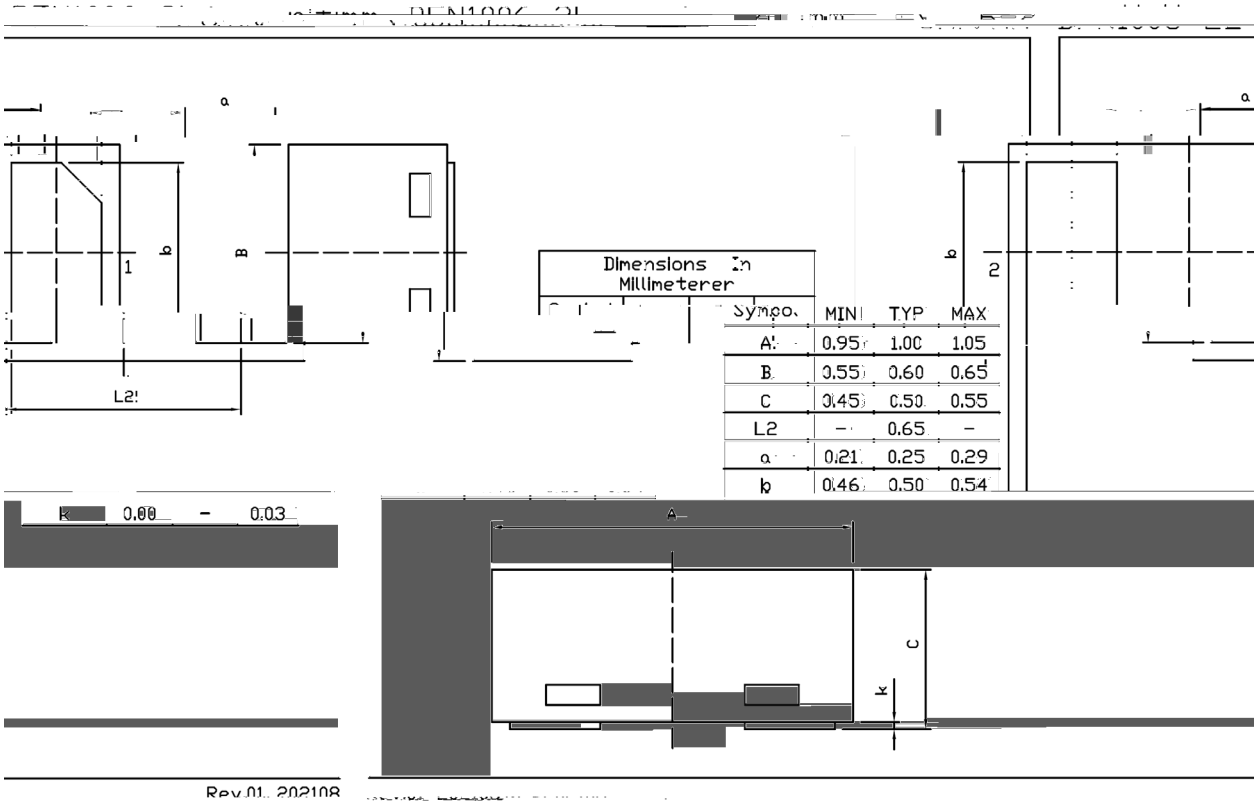
1) V_{BR} is measured with a pulse test current IT at an ambient temperature of 25 ɬ .

2) Non-repetitive current pulse, according to IEC61000-4-5.

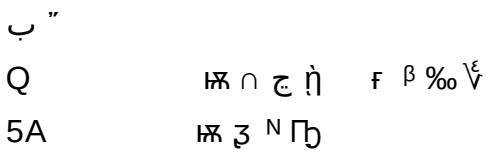
/ Electrical Characteristic Curve



/ Package Dimensions



/ Marking Instructions



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Note

BRESD5V0L1B2ZPQ

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